

Abstract Submitted
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The Carrier Recombination Of InAs/GaAs Quantum Dots CHE-
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In this study, the Time-Correlated Single Photo Counting (TCSPC) technique was
used to measure the photoluminescence (PL) spectra and time-resolved PL spectra
of InAs/GaAs QDs. Results showed that at temperatures below 50K, the lifetime
of QDs are below 2ns in the infrared region. However, at temperatures over 50K,
lifetimes exceeding 2ns can be observed. As the temperature was increased from
14K to 100K the lifetime also increases. Finally, when we fixed the temperature at
100K, we observed that the lifetime increased as the wavelength was increased.

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